

## N-Channel Power MOSFET

Primary characteristics			
Symbol	Parameter	Value	Unit
$I_D$	Continuous drain current ( $T_A=25^\circ\text{C}$ )	12	A
$V_{DS}$	Drain-source voltage	20	V
$R_{DS(ON)}$	Max drain-source on-state resistance ( $V_{GS}=4.5\text{V}$ )	11	m $\Omega$

### Features

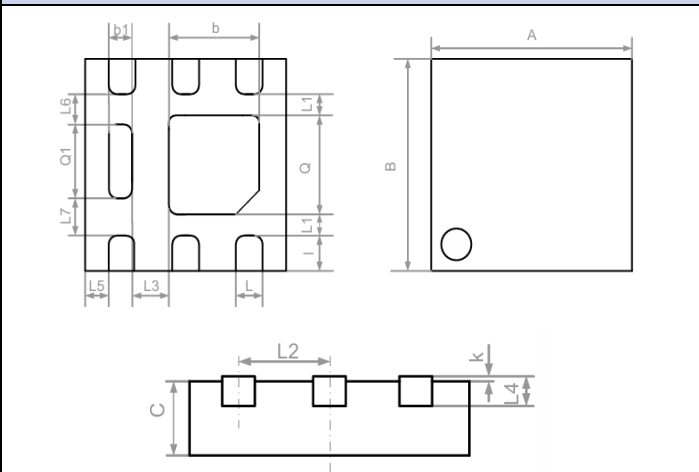
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

### Applications

- Load/Power Switching
- PWM applications

### Mechanical Data

- **Case:** SOT-23 (plastic package).  
Lead free; RoHS compliant; Halogen free
- **Molding Compound Flammability Rating:**  
UL 94 V-0
- **Terminals:** High temperature soldering guaranteed:  
260°C/10 sec. at terminals

Case dimensions																	
																	
<b>DFN2020-6L</b>																	
Unit mm	A	Q	Q1	B	b	b1	C	I	k	L	L1	L2	L3	L4	L5	L6	L7
MIN	1.95	0.9	0.72	1.95	0.85	0.13	0.45	0.25	0.00	0.25	0.1	0.65	0.3	0.15	0.12	0.15	0.23
MAX	1.05	1.1	0.92	2.05	1.05	0.33	0.55	0.35	0.05	0.35	0.3	TYP	0.5	TYP	0.32	0.35	0.43

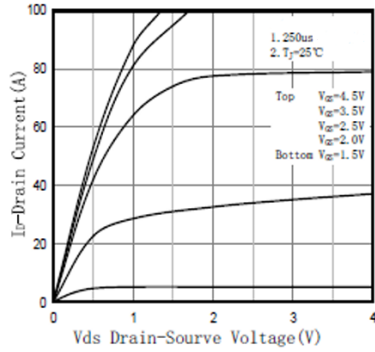
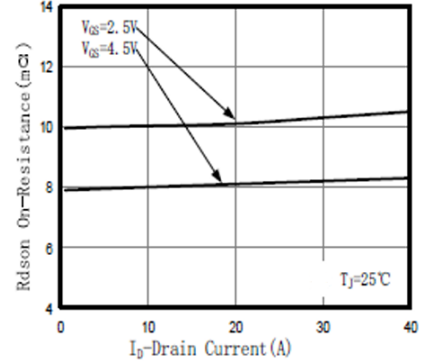
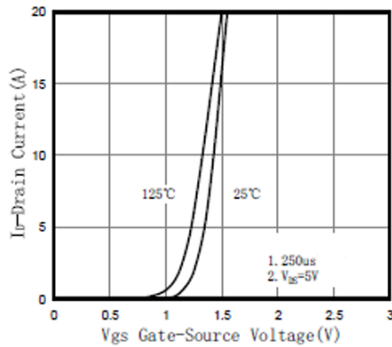
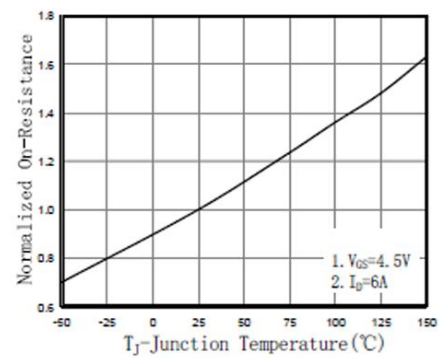
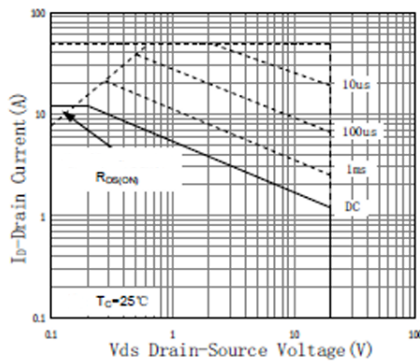
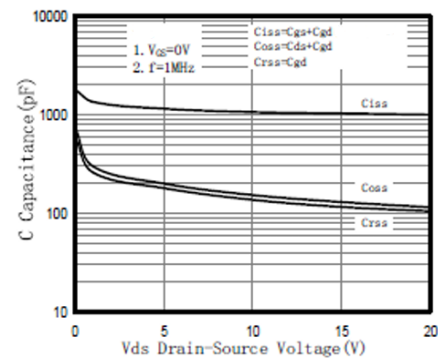
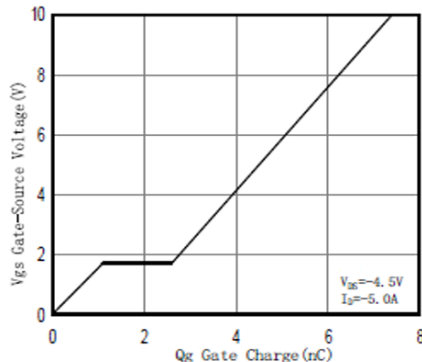
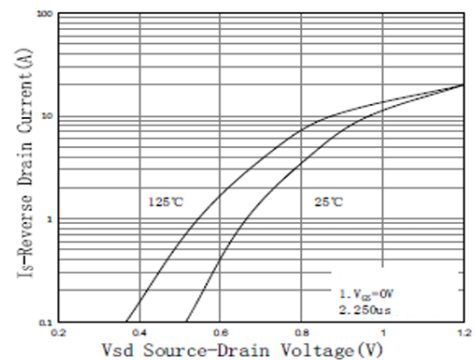
Absolute maximum ratings ( $T_A = 25^\circ\text{C}$ unless otherwise specified)				
Parameter		Symbol	Limit	Unit
Drain-source voltage		$V_{DS}$	20	V
Gate-source voltage		$V_{GS}$	$\pm 12$	V
Continuous drain current ( $T_J=150^\circ\text{C}$ ) <sup>1)</sup>	$T_A=25^\circ\text{C}$	$I_D$	12	A
	$T_A=70^\circ\text{C}$		9.6	
Pulsed drain current <sup>2)</sup>		$I_{DM}$	48	A
Power dissipation <sup>1)</sup>	$T_A=25^\circ\text{C}$	$P_D$	1.5	W
	$T_A=70^\circ\text{C}$		0.95	
Operating junction and storage temperature range		$T_J, T_{stg}$	-55~+150	$^\circ\text{C}$

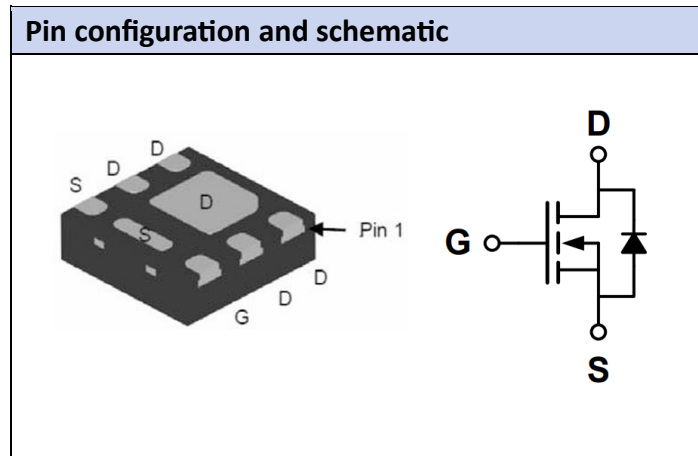
Thermal characteristics					
Parameter		Symbol	Typ	Max	Unit
Maximum junction-to-ambient <sup>1)</sup>	≤ 10s	R <sub>θJA</sub>	28	36	°C/W
	Steady-State		58	75	
Maximum junction-to-foot	Steady-State	R <sub>θJC</sub>	5.3	6.5	°C/W

Notes:  
<sup>1)</sup> Surface mounted on 1" x 1" FR4 board  
<sup>2)</sup> Pulse width limited by maximum junction temperature

Electrical characteristics (T <sub>A</sub> = 25°C unless otherwise specified)						
Parameter	Test condition	Symbol	Value			Unit
			Min	Typ	Max	
<b>OFF characteristics</b>						
Drain-source breakdown voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	BV <sub>DSS</sub>	20	-	-	V
Zero gate voltage drain current	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V	I <sub>DSS</sub>	-	-	1	μA
Gate-body leakage	V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V	I <sub>GSS</sub>	-	-	±100	nA
<b>ON characteristics</b>						
Gate threshold voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	V <sub>GS(th)</sub>	0.4	0.8	1.2	V
Drain-source on-state resistance <sup>1)</sup>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	R <sub>DS(ON)</sub>	-	8	11	mΩ
	V <sub>GS</sub> =2.5V, I <sub>D</sub> =5A		-	10	15	
<b>Dynamic characteristics <sup>2)</sup></b>						
Input capacitance	V <sub>DS</sub> =10V V <sub>GS</sub> =0V f=1.0MHz	C <sub>ISS</sub>	-	1062	-	pF
Output capacitance		C <sub>OSS</sub>	-	153	-	
Reverse transfer capacitance		C <sub>RSS</sub>	-	137	-	
<b>Switching characteristics</b>						
Turn-on delay time	V <sub>DS</sub> =10V I <sub>D</sub> =15A V <sub>GEN</sub> =4.5V R <sub>GEN</sub> =3Ω	t <sub>D(ON)</sub>	-	6	-	nS
Rise time		t <sub>r</sub>	-	17	-	
Turn-off delay time		t <sub>D(OFF)</sub>	-	28	-	
Fall time		t <sub>f</sub>	-	9	-	
Total gate charge	V <sub>DS</sub> =10V I <sub>D</sub> =15A V <sub>GS</sub> =4.5V	Q <sub>g</sub>	-	12	-	nC
Gate-source charge		Q <sub>gs</sub>	-	2	-	
Gate-drain charge		Q <sub>gd</sub>	-	3	-	
<b>Drain-source diode characteristics</b>						
Diode forward voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =6A	V <sub>SD</sub>	-	-	1.2	V

Notes:  
<sup>1)</sup> Pulse test: Pulse width ≤ 300μs, duty cycle ≤ 2%  
<sup>2)</sup> Guaranteed by design, not subject to production testing

**Typical characteristics ( $T_A = 25^\circ\text{C}$  unless otherwise specified)**
**Output characteristics**

**On-resistance vs. Drain current**

**Transfer characteristic**

**On-resistance vs. Junction temperature**

**Safe operating area**

**Capacitance characteristics**

**Gate-charge characteristic**

**Body diode characteristics**




Ordering information			
Part Number	Package	Packaging option	Shipping Quantity
AKXF12N02D	DFN2020-6L	Tape and reel	3000 pcs / reel

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